



#### SYNCHRONOUS MOSFET CONTROLLER IN SOT26

## **Description**

The ZXGD3113W6 is intended to drive a MOSFET configured as an ideal diode replacement. The device is comprised of a differential amplifier detector stage and high current driver. The detector monitors the reverse voltage of the MOSFET, such that if the body diode conduction occurs, a positive voltage is applied to the MOSFET's Gate Pin.

Once the positive voltage is applied to the Gate, the MOSFET switches on. The detector's output voltage is then proportional to the MOSFET Drain-Source voltage, and this is applied to the Gate via the driver. This action provides a rapid MOSFET turn-off at zero Drain current.

## **Applications**

Flyback Converters

#### **Features**

- 3.5V to 40V V<sub>CC</sub> Range
- Operating up to 250kHz
- Suitable for Discontinuous Conduction Mode (DCM), Critical Conduction Mode (CrCM), and Continuous Conduction Mode (CCM) Operation
- Proportional Gate Drive Control
- Detector Threshold Voltage: -10mV
- Standby Current: 6mA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

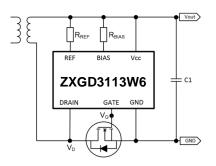
#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.018 grams (Approximate)

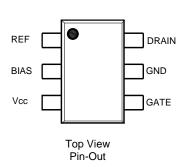
SOT26

Top View

#### **Typical Configuration**



#### SOT26



#### **Ordering Information** (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXGD3113W6-7	2B2	7	8	3000

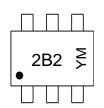
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



## **Marking Information**

#### SOT26

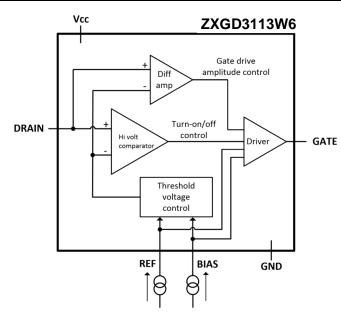


2B2 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: E = 2017) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2017	2	018	2019	2020	2021	2022	2023	3 20	24 2	2025	2026	2027
Code	Е		F	G	Н		J	K	L	-	M	N	0
Month	ı	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	!	1	2	3	4	5	6	7	8	9	0	N	D

# **Functional Block Diagram**



Pin Number	Name	Description and Function
1	REF	Reference This pin is connected to V <sub>CC</sub> via a resistor, R <sub>REF</sub> . R <sub>REF</sub> sets the source current into this pin
2	BIAS	Bias This pin is connected to V <sub>CC</sub> via a resistor, R <sub>BIAS</sub> . R <sub>BIAS</sub> sets the source current into this pin.
3	Vcc	Power Supply This is the supply pin. It is recommended to decouple this point to Ground closely with a ceramic capacitor.
4	GATE	Gate Drive This pin sources and sinks current to and from the synchronous MOSFET Gate.
5	GND	Ground This is the ground reference point. Connect to the synchronous MOSFET Source terminal.
6	DRAIN	Drain This pin is connected to the Drain pin of the synchronous MOSFET.



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage, Relative to GND	Vcc	40	V
Drain Pin Voltage	V <sub>D</sub>	-3 to 160	V
Gate Output Voltage	$V_{G}$	-3 to V <sub>CC</sub> +3	V
Gate Driver Peak Source Current	Isource	1.5	Α
Gate Driver Peak Sink Current	I <sub>SINK</sub>	3	Α
Reference Voltage	$V_{REF}$	V <sub>CC</sub>	V
Reference Current	I <sub>REF</sub>	25	mA
Bias Voltage	V <sub>BIAS</sub>	Vcc	V
Bias Current	I <sub>BIAS</sub>	100	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		500 5	
	(Note 6)		731	-
Power Dissipation	(Note 6)	6	5.8	mW
Linear Derating Factor	(Note 7)	$P_{D}$	868	mW/°C
	(Note 1)		6.9	
	(Note 8)		1016	
			8.1	
	(Note 5)		250	
Thermal Resistance, Junction to Ambient	(Note 6)	D	171	°C/W
Thermal itesistance, sunction to Ambient	(Note 7)	$R_{ heta JA}$	144	C/VV
	(Note 8)		123	
Thermal Resistance, Junction to Lead	$R_{ heta JL}$	105	°C/W	
Operating Temperature Range	TJ	-40 to +150	°C	
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	C	

## ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Charged Device Model	ESD CDM	1000	V	IV
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

#### Notes:

- 5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except Pin 3 (Vcc) and Pin 2 (BIAS) are both connected to separate 5mm x 5mm 1oz copper heatsinks.
- 7. Same as Note 6, except both heatsinks are 10mm x 10mm.
  8. Same as Note 6, except both heatsinks are 15mm x 15mm.
- 9. Thermal resistance from junction to solder-point at the end of each lead on Pin 3 (VCC) and Pin 2 (Bias).
- 10. Refer to JEDEC specification JESD22-A114 JESD22-A115 and JESD22-C101.

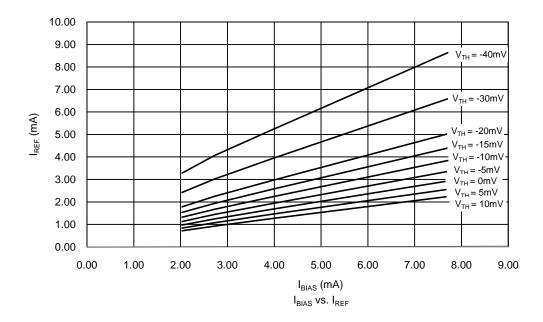


## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

 $V_{CC} = 19V$ ;  $R_{BIAS} = 4.7k\Omega$ ;  $R_{REF} = 8.2k\Omega$ 

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Input and Supply						
Quiescent Current	ΙQ	_	6.2	_	mA	$V_D \ge 0V$
Gate Driver					•	
Turn-Off Threshold Voltage	$V_{T}$	-20	-10	0	mV	$V_G = 1V$
	V <sub>G(OFF)</sub>	0	0.73	1.0		V <sub>D</sub> ≥ 1V
Gate Output Voltage	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	12.5	13.8	V <sub>CC</sub>	V	$V_D = -50 \text{mV}$
	V <sub>G</sub>	17	17.8	Vcc		V <sub>D</sub> = -100mV
Switching Performance for C <sub>LOAD</sub> = 10nF						
Turn-On Propagation Delay	t <sub>D(RISE)</sub>	_	250	_		
Turn-Off Propagation Delay	t <sub>D(FALL)</sub>	_	27	_		
Gate Rise Time		_	187	_	ns	From 10% of V <sub>G</sub> to 10V
Gate Rise Time	t <sub>R</sub>	_	360	_		From 10% to 90% of V <sub>G</sub>
Gate Fall Time	t <sub>F</sub>	_	210	_		From 90% to 10% of V <sub>G</sub>
Source Current	I <sub>SOURCE</sub>	_	0.5	_	_	Canaditive Load of 10nF
Sink Current	Isink	_	1.5	_	A	Capacitive Load of 10nF

# Threshold Settings Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

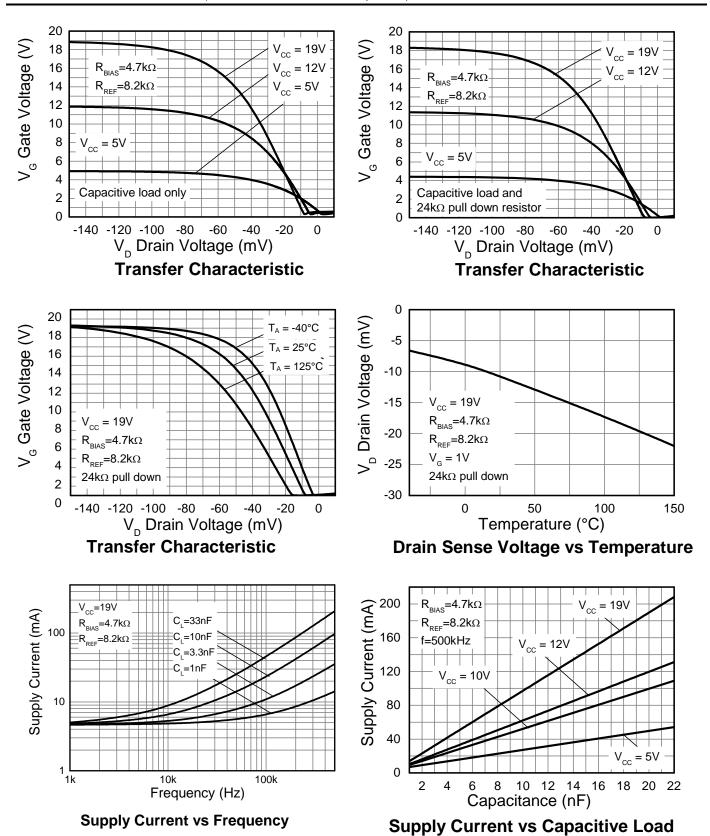


 $R_{BIAS} = \sim (V_{CC} - 0.5)/I_{BIAS}$ 

 $R_{REF} = \sim (V_{CC} - 0.7)/I_{REF}$ 

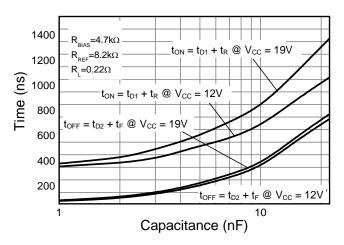


#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

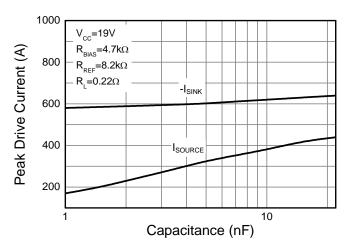




# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.) (Cont.)



**Switching vs Capacitive Load** 



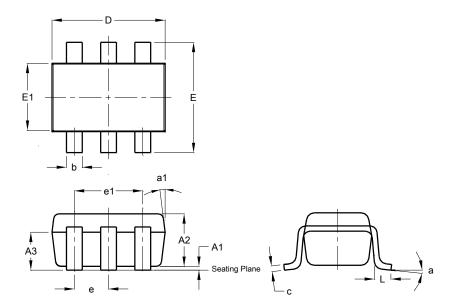
**Gate Current vs Capacitive Load** 



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT26

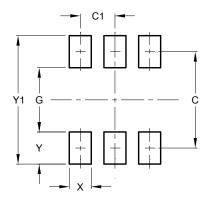


	SOT26							
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
А3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
С	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	-	-	0.95					
e1	-	-	1.90					
Е	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	-	-	8°					
a1	-	-	7°					
All	Dimen	sions i	in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
X	0.55
Υ	0.80
Y1	3.20

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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